ESJA57-04A

5mA Axial Leaded High Voltage Silicon Diode

Features

Mechanical Data

- Weight: 0.2 grams (approx.)
- Vibration Proof:5 G

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Items	Conditions	Symbols	Ratings	Units
Repetitive peak reverse voltage		V_{RRM}	4	KV peak
Non-repetitive peak forward current	50Hz Sine-half wave peak value	I_{FSM}	0.5	A peak
Average forward current	50Hz Sine-wave	I_{AV}	5	mA
Allowable junction temperature		Tj	120	°C
Storage Temperature range		Tstg	-40—120	°C
Allowable operating case temperature		Tc	100	°C
Maximum forward voltage drop	1F=10mA	VF	15	V
Maximum reverse current	VR=4KV	IR_1	2	uA
Maximum reverse current	VR=4KV ,100°C	IR_2	5	uA
Maximum reverse recovery time	1F=2mA,1R=4mA	Trr	0.08	uS
Maximum junction capacitance	F=1MHz,VR=0V	Cj	2	PF

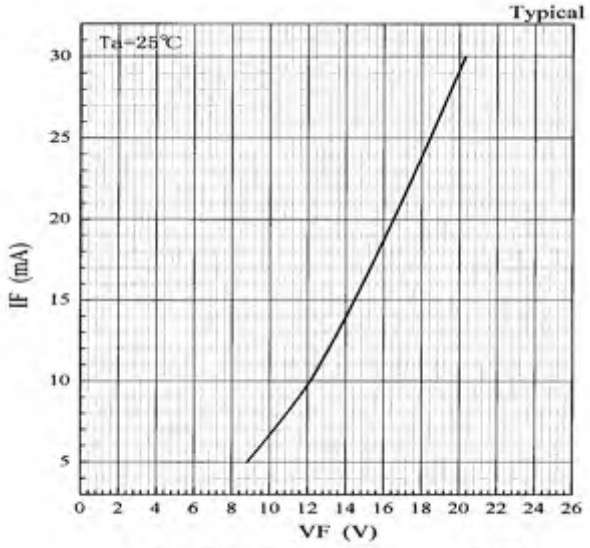


Fig.1 Forward characteristic[VF-IF]

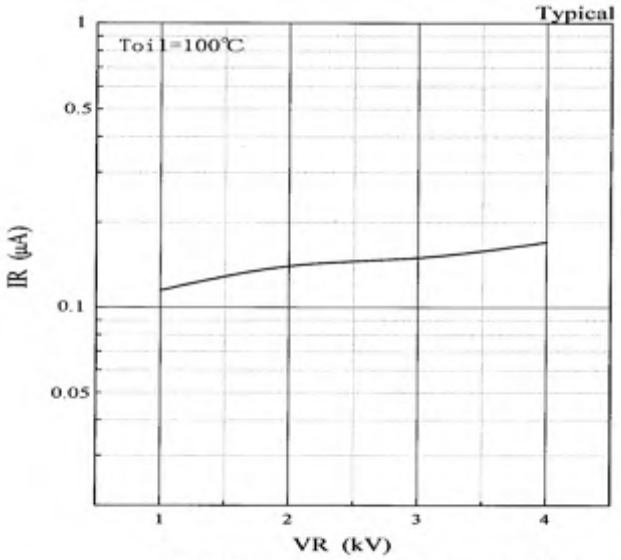


Fig.2 Reverse characteristic[VR-IR]

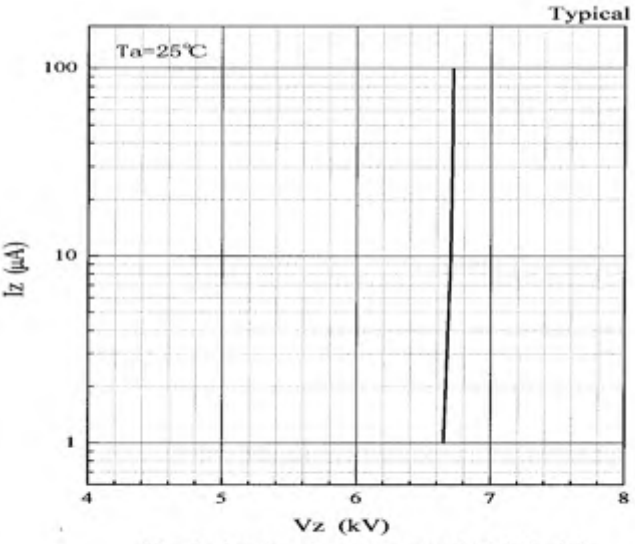


Fig.3 Avalanche characteristic[Vz-Iz]

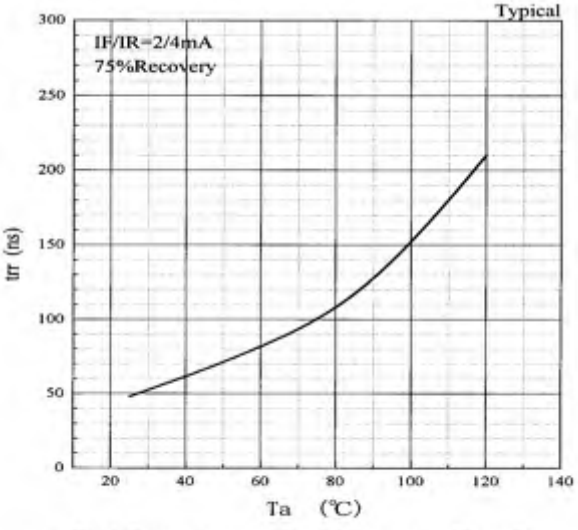


Fig.4 Reverse recovery time characteristic[Ta-trr]